

# Adrianagrazia Passaseo

## List of Publications by Year in descending order

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203  
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186265

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docs citations

204  
times ranked

3291  
citing authors

#	ARTICLE	IF	CITATIONS
1	Nanoscale 3D Chiral Plasmonic Helices with Circular Dichroism at Visible Frequencies. ACS Photonics, 2015, 2, 105-114.	6.6	211
2	Triple-helical nanowires by tomographic rotatory growth for chiral photonics. Nature Communications, 2015, 6, 6484.	12.8	145
3	Three Dimensional Chiral Metamaterial Nanospirals in the Visible Range by Vertically Compensated Focused Ion Beam Induced Deposition. Advanced Optical Materials, 2014, 2, 154-161.	7.3	110
4	Programmable Extreme Chirality in the Visible by Helix-Shaped Metamaterial Platform. Nano Letters, 2016, 16, 5823-5828.	9.1	71
5	Capture and thermal re-emission of carriers in long-wavelength InGaAs/GaAs quantum dots. Applied Physics Letters, 2001, 79, 3968-3970.	3.3	64
6	Stress-driven AlN cantilever-based flow sensor for fish lateral line system. Microelectronic Engineering, 2011, 88, 2376-2378.	2.4	64
7	Materials and 3D Designs of Helix Nanostructures for Chirality at Optical Frequencies. Advanced Optical Materials, 2017, 5, 1601079.	7.3	61
8	Biomolecular Sensing at the Interface between Chiral Metasurfaces and Hyperbolic Metamaterials. ACS Applied Materials & Interfaces, 2020, 12, 30181-30188.	8.0	55
9	Toward Cavity Quantum Electrodynamics with Hybrid Photon Gap-Plasmon States. ACS Nano, 2016, 10, 11360-11368.	14.6	53
10	Wavelength control from 1.25 to 1.4 $\mu\text{m}$ in In <sub>x</sub> Ga <sub>1-x</sub> As quantum dot structures grown by metal organic chemical vapor deposition. Applied Physics Letters, 2001, 78, 1382-1384.	3.3	50
11	Fabrication of force sensors based on two-dimensional photonic crystal technology. Microelectronic Engineering, 2007, 84, 1450-1453.	2.4	49
12	Nanoscale Study of the Tarnishing Process in Electron Beam Lithography-Fabricated Silver Nanoparticles for Plasmonic Applications. Journal of Physical Chemistry C, 2016, 120, 24314-24323.	3.1	49
13	Aluminum Nitride piezo-MEMS on polyimide flexible substrates. Microelectronic Engineering, 2011, 88, 2372-2375.	2.4	43
14	Tailoring chiro-optical effects by helical nanowire arrangement. Nanoscale, 2015, 7, 18081-18088.	5.6	43
15	Structural study of InGaAs/GaAs quantum dots grown by metalorganic chemical vapor deposition for optoelectronic applications at 1.3 $\mu\text{m}$ . Journal of Applied Physics, 2001, 89, 4341-4348.	2.5	41
16	Protein Conduction and Negative Differential Resistance in Large-Scale Nanojunction Arrays. Small, 2007, 3, 1184-1188.	10.0	40
17	High temperature characterization of GaN-based photodetectors. Sensors and Actuators A: Physical, 2004, 113, 329-333.	4.1	39
18	AlN on polysilicon piezoelectric cantilevers for sensors/actuators. Microelectronic Engineering, 2009, 86, 1204-1207.	2.4	39

#	ARTICLE	IF	CITATIONS
19	Fabrication of 3D metallic photonic crystals by X-ray lithography. <i>Microelectronic Engineering</i> , 2003, 67-68, 479-486.	2.4	38
20	Symmetry Breaking in Oligomer Surface Plasmon Lattice Resonances. <i>Nano Letters</i> , 2019, 19, 1922-1930.	9.1	37
21	High-modal gain 1300-nm In(Ga)As-GaAs quantum-dot lasers. <i>IEEE Photonics Technology Letters</i> , 2006, 18, 1735-1737.	2.5	33
22	Phase-locked mutually coupled 1.3 $\mu\text{m}$ quantum-dot lasers. <i>Optics Letters</i> , 2007, 32, 3245.	3.3	33
23	Freestanding piezoelectric rings for high efficiency energy harvesting at low frequency. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	33
24	Three-dimensional nanohelices for chiral photonics. <i>Applied Physics A: Materials Science and Processing</i> , 2016, 122, 1.	2.3	33
25	3-D FEM Modeling and Fabrication of Circular Photonic Crystal Microcavity. <i>Journal of Lightwave Technology</i> , 2008, 26, 2960-2968.	4.6	32
26	Comparison of radiative and structural properties of 1.3 $\mu\text{m}$ In <sub>x</sub> Ga(1-x)As quantum-dot laser structures grown by metalorganic chemical vapor deposition and molecular-beam epitaxy: Effect on the lasing properties. <i>Applied Physics Letters</i> , 2003, 82, 3632-3634.	3.3	31
27	Second-harmonic generation in reflection and diffraction by a GaAs photonic-crystal waveguide. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2002, 19, 2122.	2.1	30
28	Oxidation kinetics of AlAs and (AlGa)As layers in GaAs-based diode laser structures: comparative analysis of available experimental data. <i>Semiconductor Science and Technology</i> , 2004, 19, 333-341.	2.0	30
29	Focused Ion Beam Processing for 3D Chiral Photonics Nanostructures. <i>Micromachines</i> , 2021, 12, 6.	2.9	30
30	Persistent photocurrent spectroscopy of GaN metal-semiconductor-metal photodetectors on long time scale. <i>Applied Physics Letters</i> , 2004, 85, 6083-6085.	3.3	28
31	Structural and optical studies of In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs multiple quantum wells. <i>Journal of Applied Physics</i> , 1996, 80, 482-489.	2.5	27
32	Long wavelength emission in In <sub>x</sub> Ga <sub>1-x</sub> As quantum dot structures grown in a GaAs barrier by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2004, 84, 1868-1870.	3.3	27
33	Optical filter based on two coupled PhC GaAs-membranes. <i>Optics Letters</i> , 2010, 35, 411.	3.3	27
34	Precise detection of circular dichroism in a cluster of nano-helices by photoacoustic measurements. <i>Scientific Reports</i> , 2017, 7, 5257.	3.3	27
35	Enhanced Performances of Quantum Dot Lasers Operating at 1.3 $\mu\text{m}$ . <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2008, 14, 1188-1196.	2.9	26
36	Femtomolar Biodetection by a Compact Core-Shell 3D Chiral Metamaterial. <i>Nano Letters</i> , 2021, 21, 6179-6187.	9.1	26

#	ARTICLE	IF	CITATIONS
37	High efficiency and high modal gain InAs/InGaAs/GaAs quantum dot lasers emitting at 1300 nm. Semiconductor Science and Technology, 2007, 22, 396-398.	2.0	25
38	Electroluminescence and Transmission Electron Microscopy Characterization of Reverse-Biased AlGaIn/GaN Devices. IEEE Transactions on Device and Materials Reliability, 2013, 13, 126-135.	2.0	25
39	Role of charge separation on two-step two photon absorption in InAs/GaAs quantum dot intermediate band solar cells. Applied Physics Letters, 2016, 108, .	3.3	25
40	Second harmonic generation in AlGaIn, GaN and Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN multiple quantum well structures. Applied Physics B: Lasers and Optics, 2004, 79, 611-615.	2.2	24
41	GaN-based surface acoustic wave filters for wireless communications. Superlattices and Microstructures, 2004, 36, 825-831.	3.1	23
42	Emission control of colloidal nanocrystals embedded in Si <sub>3</sub> N <sub>4</sub> photonic crystal H1 nanocavities. Microelectronic Engineering, 2010, 87, 1435-1438.	2.4	23
43	Dominance of charged excitons in single-quantum-dot photoluminescence spectra. Physical Review B, 2002, 66, .	3.2	22
44	High-Performance Directly Modulated 1.3- $\mu$ m Undoped InAs-InGaAs Quantum-Dot Lasers. IEEE Photonics Technology Letters, 2007, 19, 191-193.	2.5	22
45	Fabrication of AlN/Si SAW delay lines with very low RF signal noise. Microelectronic Engineering, 2007, 84, 1320-1324.	2.4	22
46	High responsivity GaN-based UV detectors. Electronics Letters, 2003, 39, 1747.	1.0	21
47	Enhanced modal gain of multilayer InAs-InGaAs-GaAs quantum dot lasers emitting at 1300nm. Journal of Applied Physics, 2006, 100, 123111.	2.5	21
48	Blue second harmonic generation from aluminum nitride films deposited onto silicon by sputtering technique. Journal of Applied Physics, 2006, 100, 023507.	2.5	20
49	Measurement of pure Kerr nonlinearity in GaN thin films at 800 nm by means of eclipsing Z-scan experiments. Journal of Optics, 2007, 9, L3-L4.	1.5	20
50	Structural and optical properties of vertically stacked triple InAs dot-in-well structure. Journal of Applied Physics, 2008, 103, .	2.5	20
51	The polarization response in InAs quantum dots: theoretical correlation between composition and electronic properties. Nanotechnology, 2012, 23, 165202.	2.6	20
52	Tailoring Electromagnetic Hot Spots toward Visible Frequencies in Ultra-Narrow Gap Al <sub>2</sub> O <sub>3</sub> Bowtie Nanoantennas. ACS Photonics, 2018, 5, 3399-3407.	6.6	20
53	Microphotoluminescence spectroscopy of vertically stacked In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs quantum wires. Physical Review B, 1998, 58, 1962-1966.	3.2	19
54	Band-gap renormalization in modulation-doped In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs V-shaped quantum wires. Physical Review B, 1999, 59, 2230-2233.	3.2	19

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55	Dependence of the emission wavelength on the internal electric field in quantum-dot laser structures grown by metal-organic chemical-vapor deposition. Applied Physics Letters, 2001, 79, 1435-1437.	3.3	19
56	Direct quantitative measurement of compositional enrichment and variations in In <sub>y</sub> Ga <sub>1-y</sub> As quantum dots. Applied Physics Letters, 2001, 79, 3170-3172.	3.3	19
57	Simultaneous filling of InAs quantum dot states from the GaAs barrier under nonresonant excitation. Applied Physics Letters, 2007, 90, 111907.	3.3	19
58	1.31- $\mu$ m InGaAs quantum dot light-emitting diodes grown directly in a GaAs matrix by metalorganic chemical-vapor deposition. Applied Physics Letters, 2004, 84, 2482-2484.	3.3	18
59	Electrically injected InGaAs/GaAs quantum-dot microcavity light-emitting diode operating at 1.3 $\mu$ m and grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 84, 4155-4157.	3.3	17
60	Hybrid polymer/semiconductor microtubes: A new fabrication approach. Microelectronic Engineering, 2008, 85, 1170-1172.	2.4	17
61	Origin of persistent photocurrent in GaN/AlGa <sub>n</sub> multiquantum wells. Journal of Applied Physics, 2001, 89, 5782-5784.	2.5	16
62	Fabrication by means of x-ray lithography of two-dimensional GaAs/AlGaAs photonic crystals with an unconventional unit cell. Nanotechnology, 2002, 13, 644-652.	2.6	16
63	Mapping the nonlinear optical susceptibility by noncollinear second-harmonic generation. Optics Letters, 2009, 34, 2189.	3.3	16
64	Flexible piezoelectric cantilevers fabricated on polyimide substrate. Microelectronic Engineering, 2012, 98, 603-606.	2.4	16
65	High quality MOCVD GaN film grown on sapphire substrates using HT-AlN buffer layer. Journal of Non-Crystalline Solids, 2006, 352, 2332-2334.	3.1	15
66	Design and fabrication of active and passive photonic crystal resonators. Microelectronic Engineering, 2006, 83, 1823-1825.	2.4	15
67	Evidence of "crossed" transitions in dots-in-a-well structures through waveguide absorption measurements. Applied Physics Letters, 2008, 93, 151112.	3.3	15
68	Investigation of different mechanisms of GaN growth induced on AlN and GaN nucleation layers. Journal of Applied Physics, 2009, 105, .	2.5	15
69	Atomic equilibrium concentrations in (InGa)As quantum dots. Applied Physics Letters, 2001, 78, 3121-3123.	3.3	14
70	3D Chiral MetaCrystals. Advanced Functional Materials, 2022, 32, 2109258.	14.9	14
71	Influence of different V-grooved GaAs substrates on the geometrical shape of InGaAs/GaAs quantum wires. Journal of Crystal Growth, 1999, 197, 777-782.	1.5	12
72	Second harmonic generation in GaN <sub>0.5</sub> Al <sub>0.5</sub> Ga <sub>0.5</sub> N <sub>0.5</sub> films deposited by metal-organic chemical vapor deposition. Applied Physics Letters, 2006, 89, 131105.	3.3	12

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73	Nanocrystals cylindrical microcavities exploiting thin-walled InGaAs/GaAs microtubes. <i>Microelectronic Engineering</i> , 2007, 84, 1408-1411.	2.4	12
74	Linear increase of the modal gain in 1.3 $\mu\text{m}$ InAs/GaAs quantum dot lasers containing up to seven-stacked QD layers. <i>Nanotechnology</i> , 2008, 19, 275401.	2.6	12
75	Self-organized growth of ZnTe nanoscale islands on (001)GaAs. <i>Applied Physics Letters</i> , 1998, 72, 359-361.	3.3	11
76	Charge storage and screening of the internal field in GaN/AlGaIn quantum wells. <i>Journal of Crystal Growth</i> , 2001, 230, 492-496.	1.5	11
77	Nanofabrication of high refractive index contrast two-dimensional photonic crystal waveguides. <i>Microelectronic Engineering</i> , 2003, 67-68, 670-675.	2.4	11
78	Fast nanopatterning of two-dimensional photonic crystals by electron beam lithography. <i>Superlattices and Microstructures</i> , 2004, 36, 265-270.	3.1	11
79	Fully integrated three-axis Hall magnetic sensor based on micromachined structures. <i>Microelectronic Engineering</i> , 2010, 87, 1217-1219.	2.4	11
80	Effects of the spontaneous polarization and piezoelectric fields on the luminescence spectra of GaN/Al <sub>0.15</sub> Ga <sub>0.85</sub> N quantum wells. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 7, 929-933.	2.7	10
81	DLTS characterization of silicon nitride passivated AlGaIn/GaN heterostructures. <i>Superlattices and Microstructures</i> , 2004, 36, 425-433.	3.1	10
82	Segregation in In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs Stranski-Krastanow layers grown by metal-organic chemical vapour deposition. <i>Philosophical Magazine</i> , 2005, 85, 3857-3870.	1.6	10
83	A fully integrated GaAs-based three-axis Hall magnetic sensor exploiting self-positioned strain released structures. <i>Journal of Micromechanics and Microengineering</i> , 2010, 20, 105013.	2.6	10
84	Nanowalled polymer microtubes fabricated by using strained semiconductor templates. <i>Nanotechnology</i> , 2010, 21, 245305.	2.6	10
85	Nanoscale compositional fluctuations in multiple InGaAs/GaAs quantum wires. <i>Journal of Applied Physics</i> , 2000, 87, 2261-2264.	2.5	9
86	The Influence of a Continuum Background on Carrier Relaxation in InAs/InGaAs Quantum Dot. <i>Nanoscale Research Letters</i> , 2007, 2, .	5.7	9
87	Control of unpolarized emission in closely stacked InAs quantum dot structure. <i>Superlattices and Microstructures</i> , 2010, 47, 72-77.	3.1	9
88	Gallium chiral nanoshaping for circular polarization handling. <i>Materials Horizons</i> , 2021, 8, 187-196.	12.2	9
89	Electro-optic properties of InGaAs/GaAs quantum wires with V-shaped profile. <i>Solid-State Electronics</i> , 1998, 42, 1239-1243.	1.4	8
90	Nanoscale Compositional Fluctuations in Single InGaAs/GaAs Quantum Dots. <i>Physica Status Solidi (B): Basic Research</i> , 2001, 224, 17-20.	1.5	8

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91	GaN optical system for CO and NO gas detection in the exhaust manifold of combustion engines. Journal of Optics, 2006, 8, S545-S549.	1.5	8
92	Design and modeling of tapered waveguide for photonic crystal slab coupling by using time-domain Hertzian potentials formulation. Optics Express, 2007, 15, 16484.	3.4	8
93	Scalar time domain modeling and coupling of second harmonic generation process in GaAs discontinuous optical waveguide. Optics Express, 2008, 16, 14496.	3.4	8
94	Inter-level carrier dynamics and photocurrent generation in large band gap quantum dot solar cell by multistep growth. Solar Energy Materials and Solar Cells, 2017, 171, 142-147.	6.2	8
95	Near-field low-temperature photoluminescence spectroscopy of single V-shaped quantum wires. Physical Review B, 1999, 60, 13335-13338.	3.2	7
96	Noise reduction in GaN-based radio frequency surface acoustic wave filters. Applied Physics Letters, 2004, 85, 1039-1041.	3.3	7
97	Optical polarization based logic functions (XOR or XNOR) with nonlinear Gallium nitride nanoslab. Optics Express, 2009, 17, 19337.	3.4	7
98	Tuning of polarization sensitivity in closely stacked trilayer InAs/GaAs quantum dots induced by overgrowth dynamics. Nanotechnology, 2014, 25, 055207.	2.6	7
99	Correlation between shape and electronic states in nanostructures. Micron, 2000, 31, 245-251.	2.2	6
100	Time-resolved magnetospectroscopy of In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs V-shaped quantum wires. Physical Review B, 2000, 61, 12658-12661.	3.2	6
101	Nano-island fabrication by electron beam lithography and selective oxidation of Al-rich AlGaAs layers for single electron device application. Microelectronic Engineering, 2002, 61-62, 651-656.	2.4	6
102	Electrical properties of planar AlGaIn/GaN Schottky diodes: Role of 2DEG and analysis of non-idealities. Journal of Applied Physics, 2017, 121, 135701.	2.5	6
103	X-ray lithography for 3D microfluidic applications. Microelectronic Engineering, 2004, 73-74, 870-875.	2.4	6
104	GaAs hall sensors made by the MOCVD technique. Sensors and Actuators A: Physical, 1992, 32, 651-655.	4.1	5
105	Fabrication of GaN/AlGaIn 1D photonic crystals designed for nonlinear optical applications. Proceedings of SPIE, 2010, , .	0.8	5
106	Thermoresistive and Piezoresistive Properties of Wurtzite N-GaN. Physica Status Solidi A, 2002, 190, 281-286.	1.7	4
107	Rapid prototyping of two-dimensional photonic crystal devices by a dual beam focused ion beam system. Microelectronic Engineering, 2005, 78-79, 417-421.	2.4	4
108	High-efficiency 1.3 $\mu$ m InGaAs/GaAs quantum-dot microcavity light-emitting diodes grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2005, 86, 151118.	3.3	4

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109	Very High Performance GaN HEMT devices by Optimized Buffer and Field Plate Technology. , 2006, , .		4
110	Characterization of Ohmic contacts on GaN/AlGaIn heterostructures. Applied Surface Science, 2006, 253, 1055-1064.	6.1	4
111	The effects of the focus ion beam milling process on the optical properties of semiconductor nanostructures. Nanotechnology, 2009, 20, 255306.	2.6	4
112	3D FEM MODELING AND TECHNOLOGY OF PIEZOELECTRIC RING MEMS ANTENNA. Progress in Electromagnetics Research C, 2011, 23, 123-135.	0.9	4
113	Experimental pressure sensing and technology of piezoelectric microwave/RF MEMS filters. International Journal of Microwave and Wireless Technologies, 2011, 3, 587-593.	1.9	4
114	Experimental Evidence of Complex Energy-Level Structuring in Quantum Dot Intermediate Band Solar Cells. ACS Applied Nano Materials, 2020, 3, 8365-8371.	5.0	4
115	A powerful and stable CO <sub>2</sub> laser for CH <sub>3</sub> OH FIR laser optical pumping. Infrared Physics, 1986, 26, 287-292.	0.5	3
116	A high power CH <sub>3</sub> OH FIR laser system with long-term stability. Journal of Infrared, Millimeter and Terahertz Waves, 1986, 7, 1677-1690.	0.6	3
117	Strain relaxation onset in multiple-quantum wells investigated by high-resolution X-ray diffraction and atomic force microscopy. Applied Surface Science, 1997, 115, 211-216.	6.1	3
118	Time resolved screening of the piezoelectric field in InGaAs/GaAs V-shaped quantum wires of variable profile. Journal of Physics Condensed Matter, 1999, 11, 5989-5997.	1.8	3
119	Electronic Levels and Recombination Lifetimes for Quantum Wires in a Magnetic Field. Physica Status Solidi A, 2000, 178, 239-242.	1.7	3
120	Effects of coupling on the structural properties of In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs 1-D and 0-D self-organized quantum structures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 87, 256-261.	3.5	3
121	Static and dynamic screening of the polarization fields in nitride nanostructures: a theoretical and experimental study. Physica B: Condensed Matter, 2002, 314, 35-38.	2.7	3
122	Second-harmonic generation measured on a GaAs photonic crystal planar waveguide. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 402-405.	2.7	3
123	Quantum dot nano-cavity emission tuned by a circular photonic crystal lattice. Microelectronic Engineering, 2007, 84, 1570-1573.	2.4	3
124	Optical system for CO and NO gas detection in the exhaust manifold of combustion engines. Energy Conversion and Management, 2007, 48, 2911-2917.	9.2	3
125	Fabrication and transport of large-scale molecular tunnel-junction arrays. Microelectronic Engineering, 2007, 84, 1585-1588.	2.4	3
126	Negative Uniaxial Crystal Behavior Of Circular Photonic Crystal. IEEE Journal of Quantum Electronics, 2008, 44, 1225-1231.	1.9	3



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127	Structural and Piezoelectric Properties of DC-Sputtered AlN Films Deposited on Different Si-Based Substrates. <i>Ferroelectrics</i> , 2009, 389, 41-48.	0.6	3
128	Bending Analysis in AlN-Based Multilayered Piezoelectric Cantilevers. <i>Ferroelectrics</i> , 2009, 389, 75-82.	0.6	3
129	Plasmonic nanostructures for enhanced light concentration devoted to photovoltaic applications. , 2010, , .		3
130	Chirality: Three Dimensional Chiral Metamaterial Nanospirals in the Visible Range by Vertically Compensated Focused Ion Beam Induced-Deposition (Advanced Optical Materials 2/2014). <i>Advanced Optical Materials</i> , 2014, 2, 198-198.	7.3	3
131	InAs/GaAs and InAlGaAs/AlGaAs quantum dot based solar cells for intermediate band operation. , 2014, , .		3
132	Dielectric and Ferroelectric Response of Multiphase Bi <sub>1-x</sub> Fe <sub>x</sub> O Ceramics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1800584.	1.8	3
133	Near-field enhancement in oxidized close gap aluminum dimers. <i>Nanotechnology</i> , 2021, 32, 025305.	2.6	3
134	Low-Temperature and Ammonia-Free Epitaxy of the GaN/AlGaN/GaN Heterostructure. <i>ACS Applied Electronic Materials</i> , 2021, 3, 5451-5458.	4.3	3
135	Recombination in InGaAs/GaAs quantum wire lasers. <i>Solid State Communications</i> , 1999, 112, 55-60.	1.9	2
136	Electro-optic low-voltage InGaAs/GaAs multiple quantum well modulator with organic-inorganic distributed Bragg reflector. <i>Superlattices and Microstructures</i> , 1999, 25, 313-317.	3.1	2
137	SI-GaAs detectors with epitaxial junction. <i>IEEE Transactions on Nuclear Science</i> , 1999, 46, 171-175.	2.0	2
138	Optical and Transport Properties of GaN/Al <sub>0.15</sub> Ga <sub>0.85</sub> N Quantum Wells. <i>Physica Status Solidi A</i> , 2000, 178, 73-78.	1.7	2
139	Effects of quantum mechanical coupling on the optical properties of vertically stacked V-groove quantum wires. <i>Journal of Applied Physics</i> , 2000, 88, 772-776.	2.5	2
140	Linear optical properties and photonic mode dispersion in GaAs/AlGaAs photonic crystal slabs. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003, 17, 418-419.	2.7	2
141	Resonant second-harmonic generation and mode dispersion in photonic crystal waveguides. <i>Physica Status Solidi (B): Basic Research</i> , 2003, 238, 428-431.	1.5	2
142	Role of excitons in the persistent photocurrent of GaN-based MSM detectors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 589-593.	0.8	2
143	1.32 $\mu$ m InAs/InGaAs/GaAs quantum dot lasers operating at room temperature with low threshold current density. , 2006, , .		2
144	Growth and nonlinear characterization of AlN/GaN structures. <i>Journal of Optics</i> , 2006, 8, S524-S527.	1.5	2

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145	High-Q factor single mode circular photonic crystal nano-resonator. Superlattices and Microstructures, 2008, 43, 507-511.	3.1	2
146	FEM Design and Modeling of $\chi^{(2)}$ Second-Harmonic Enhancement in Circular Photonic Crystal. Journal of Lightwave Technology, 2009, 27, 4262-4268.	4.6	2
147	Artificial Anisotropy in Circular Photonic Crystals and Applications. IEEE Nanotechnology Magazine, 2010, 9, 157-169.	2.0	2
148	Optical axis misalignment detection by noncollinear second-harmonic generation. Journal of the Optical Society of America B: Optical Physics, 2014, 31, 26.	2.1	2
149	Nonlinear absorption and gain in InGaAs/GaAs quantum wells. Applied Physics Letters, 1997, 71, 915-917.	3.3	1
150	TEM characterization of single and multiple InGaAs/GaAs quantum wires grown by metal-organic vapor phase epitaxy on V-grooved substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 67, 39-45.	3.5	1
151	Fabrication and characterization of strained InGaAs quantum wires grown on high index V-grooved GaAs substrates by LP-MOVPE. Superlattices and Microstructures, 1999, 25, 481-485.	3.1	1
152	Excitonic and Free Carrier Recombination in In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs V-Shaped Quantum Wire for Different In Content. Physica Status Solidi A, 2000, 178, 243-248.	1.7	1
153	Time-resolved magneto-optical properties of V-shaped single quantum wires. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 536-540.	2.7	1
154	Influence of the N <sub>2</sub> /H <sub>2</sub> ratio on the structural features of In <sub>x</sub> Ga <sub>1-x</sub> N/GaN films grown by MOCVD. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 87, 237-243.	3.5	1
155	Luminescence Following Highly Localized Hole Carrier Injection into InGaAs Quantum Dots. Japanese Journal of Applied Physics, 2002, 41, 5127-5128.	1.5	1
156	Light emission tuning of In <sub>0.5</sub> Ga <sub>0.5</sub> As/In <sub>0.05</sub> Ga <sub>0.95</sub> As quantum dots by a two-dimensional photonic crystal. Microelectronic Engineering, 2003, 67-68, 832-837.	2.4	1
157	Improved performances of 1.3 $\mu$ m InGaAs QD structures grown at high temperature by metal organic chemical vapour deposition. Microelectronics Journal, 2005, 36, 180-182.	2.0	1
158	Epitaxial Al/GaN and Au/GaN junctions on as-grown GaN(0001) 1 Å <sup>-1</sup> surfaces. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 804-807.	1.8	1
159	An experimental setup for room temperature waveguide spectroscopy of self-assembled quantum dots. Journal of Optics, 2006, 8, S514-S517.	1.5	1
160	Picosecond timescale carrier dynamics of InAs quantum dots: The role of a continuum background. Superlattices and Microstructures, 2008, 43, 445-448.	3.1	1
161	Comparison of Cu-gate and Ni/Au-gate GaN HEMTs large signal characteristics. , 2009, , .		1
162	Fabrication of BAW Resonators Based on Piezoelectric AlN and Reflector-on-Membrane Structure. Ferroelectrics, 2009, 389, 32-40.	0.6	1

#	ARTICLE	IF	CITATIONS
163	Circuit Modeling of Discontinuous Planar Waveguides at High Frequencies. Journal of Computational and Theoretical Nanoscience, 2009, 6, 172-177.	0.4	1
164	Polymeric rolled-up microtubes by using strained semiconductor templates. Microelectronic Engineering, 2011, 88, 2211-2213.	2.4	1
165	Understanding polarization properties of InAs quantum dots by atomistic modeling of growth dynamics. AIP Conference Proceedings, 2013, , .	0.4	1
166	InAs/AlGaAs quantum dots grown by a novel molecular beam epitaxy multistep design for intermediate band solar cells: physical insight into the structure, composition, strain and optical properties. CrystEngComm, 2019, 21, 4644-4652.	2.6	1
167	Design of two-dimensional photonic-crystal mirrors for InGaAs QW laser applications. Microelectronic Engineering, 2004, 73-74, 377-382.	2.4	1
168	Preparation and test of special surfaces for epi-ready InP wafers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 44, 213-216.	3.5	0
169	Quantum-well optoelectronic modulators in high magnetic field: A technological issue for the operation in particle accelerators. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1997, 390, 237-240.	1.6	0
170	Optical processes and electronic states in InGaAs/GaAs V-groove quantum wire lasers. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 1999, 55, 1923-1929.	3.9	0
171	Nonlinear properties in In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs multiple quantum well laser structures. Superlattices and Microstructures, 1999, 25, 397-400.	3.1	0
172	Electron-Hole Dynamics in MOCVD-Grown InGaAs/GaAs Quantum Dots Emitting at 1.3 μm. Physica Status Solidi A, 2002, 190, 561-564.	1.7	0
173	Open issues for lasing at 1.3 μm in MOCVD-grown quantum dots. Physica Status Solidi (B): Basic Research, 2003, 238, 349-352.	1.5	0
174	Nonlinear optical response in patterned planar waveguides. , 0, , .		0
175	Characterisation of the Nonlinear Coefficients of AlGaIn/GaN Crystalline Thin Films Via SHG Measurements. AIP Conference Proceedings, 2004, , .	0.4	0
176	Tuning of long-wavelength emission in In <sub>x</sub> Ga <sub>1-x</sub> As quantum dot structures. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 23, 390-395.	2.7	0
177	Trapping mechanisms of persistent photocurrent in GaN-based MSM detectors. , 2004, , .		0
178	InGaAs quantum dot structures grown in GaAs barrier by metal-organic chemical vapor deposition for high-efficient long-wavelength emission. , 2004, 5361, 44.		0
179	Photomodulated reflectance studies of quantum dot in MCLED structures: monitoring cavity-ground state exciton resonance. Microelectronics Journal, 2005, 36, 200-202.	2.0	0
180	High-gain low-threshold InAs/InGaAs/GaAs quantum dot lasers emitting around 1300 nm. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 4027-4030.	0.8	0

#	ARTICLE	IF	CITATIONS
181	High Gain 1300 nm Quantum Dot Lasers. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	0
182	Photoreflectance symmetry and amplitude study of quantum dots in microcavity light emitting diode structure: The cavity-ground state exciton resonance. Journal of Applied Physics, 2007, 101, 024511.	2.5	0
183	High Gain and High Speed 1.3 $\mu\text{m}$ InAs/InGaAs Quantum Dot Lasers. , 2007, , .		0
184	1.3 micron high modal gain quantum dot lasers. , 2008, , .		0
185	Design criteria and 3D FEM modeling of air hole photonic crystal. , 2008, , .		0
186	Mechanical Behaviour of Hybrid Polymer/Semiconductor Microtubes. Ferroelectrics, 2009, 391, 168-174.	0.6	0
187	Novel Time-Domain Circuit Modelling of $\chi^{(2)}$ Nonlinear Process in Periodic Optical Waveguide. Ferroelectrics, 2009, 390, 62-70.	0.6	0
188	Novel grating design approach by radiation modes coupling in nonlinear optical waveguides. Optics Express, 2009, 17, 6982.	3.4	0
189	Properties of quadratic noncollinear interaction of GaN based structures. , 2009, , .		0
190	Design and modeling of $\chi^{(2)}$ second harmonic amplification in circular photonic crystal. Proceedings of SPIE, 2009, , .	0.8	0
191	Double grating design of 3D phase matched waveguide for second harmonic $\chi^{(2)}$ process. Proceedings of SPIE, 2009, , .	0.8	0
192	Double Grating Design and Modeling of Second Harmonic Enhancement by Radiation Coupling in Nonlinear Optical Waveguides. Journal of Computational and Theoretical Nanoscience, 2009, 6, 2170-2178.	0.4	0
193	Transverse Resonance Circuit Modeling and Hertzian Potential Formulation for Integrated Optical Waveguides. Journal of Computational and Theoretical Nanoscience, 2009, 6, 1452-1457.	0.4	0
194	Near Field and Optical Diffraction of 3D Dielectric Corner by Transmission Line Modeling and Multipole Expansion of Green's Function. Journal of Computational and Theoretical Nanoscience, 2009, 6, 1075-1080.	0.4	0
195	Design and Optimisation of WDM Circular Photonic Crystals Characterised by Induced Anisotropy. Journal of Computational and Theoretical Nanoscience, 2010, 7, 1848-1854.	0.4	0
196	Bragg reflector by means of the form birefringence effect in dielectric rings. Superlattices and Microstructures, 2010, 47, 219-224.	3.1	0
197	Design of nonlinear GaAs/AlGaAs second harmonic converters. Superlattices and Microstructures, 2010, 47, 108-117.	3.1	0
198	Energy detection and radiation by metallic rings embedded into a self-rolled $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ micro-tube. , 2010, , .		0

#	ARTICLE	IF	CITATIONS
199	GaN/AlGaIn microcavities for enhancement of nonlinear optical effects. Proceedings of SPIE, 2010, , .	0.8	0
200	Optical filter based on a coupled bilayer photonic crystal. Microelectronic Engineering, 2011, 88, 2771-2774.	2.4	0
201	Different values for the linewidth enhancement factor of a Quantum-Dots laser obtained using optical and electrical modulation. , 2013, , .		0
202	Accurate design and modeling of $\chi^{(2)}$ nonlinear processes in periodic waveguides by Hertzian potential method. Proceedings of SPIE, 2009, , .	0.8	0
203	Low-density self-assembled InGaAs QDs grown directly in a GaAs matrix for quantum-communication applications at 1300 nm wavelength. Microelectronic Engineering, 2004, 73-74, 757-761.	2.4	0